



# JCS1HN60C

## 主要参数 MAIN CHARACTERISTICS

$I_D$	0.5 A	TO-92
$V_{DSS}$	600 V	
$R_{dson}(@V_{gs}=10V)$	15 $\Omega$	
$Q_g$	3.6 nC	

### 用途

- 高频开关电源
- 电子镇流器

### APPLICATIONS

- High efficiency switch mode power supplies
- Electronic lamp ballasts based on half bridge

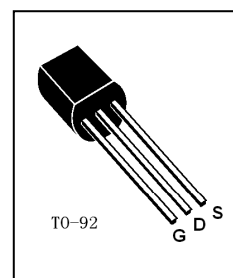
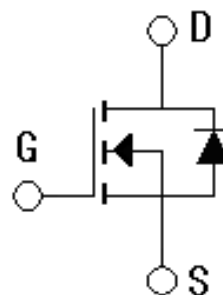
### 产品特性

- 低栅极电荷
- 低  $C_{rss}$  (典型值 2.8pF)
- 开关速度快
- 产品全部经过雪崩测试
- 高抗 dv/dt 能力
- RoHS 产品

### FEATURES

- Low gate charge
- Low  $C_{rss}$  (typical 2.8pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability
- RoHS product

### 封装 Package



## 订货信息 ORDER MESSAGE

订货型号 Order codes	印记 Marking	封装 Package	无卤素 Halogen Free	包装 Packaging	器件重量 Device Weight
JCS1HN60TC-O-T-N-A	JCS1HN60C	TO-92	否 NO	编带 Brede	0.216 g(typ)
JCS1HN60TC-R-T-N-A	JCS1HN60C	TO-92	YES NO	编带 Brede	0.216 g(typ)





## 绝对最大额定值 ABSOLUTE RATINGS (Tc=25℃)

项 目 Parameter	符 号 Symbol	数 值 Value	单 位 Unit
		JCS1HN60C	
最高漏极-源极直流电压 Drain-Source Voltage	V <sub>DSS</sub>	600	V
连续漏极电流 Drain Current -continuous	I <sub>D</sub> T=25℃ T=100℃	0.5	A
		0.31	A
最大脉冲漏极电流 (注1) Drain Current - pulse (note 1)	I <sub>DM</sub>	2.0	A
最高栅源电压 Gate-Source Voltage	V <sub>GSS</sub>	±30	V
单脉冲雪崩能量 (注2) Single Pulsed Avalanche Energy (note 2)	E <sub>AS</sub>	20	mJ
雪崩电流 (注1) Avalanche Current (note 1)	I <sub>AR</sub>	1.0	A
重复雪崩能量 (注1) Repetitive Avalanche Energy (note 1)	E <sub>AR</sub>	2.0	mJ
二极管反向恢复最大电压变化速率 (注3) Peak Diode Recovery dv/dt (note 3)	dv/dt	4.2	V/ns
耗散功率 Power Dissipation	P <sub>D</sub> T <sub>C</sub> =25℃ -Derate above 25℃	3.0	W
		0.025	W/℃
最高结温及存储温度 Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55~+150	℃
引线最高焊接温度 Maximum Lead Temperature for Soldering Purposes	T <sub>L</sub>	300	℃





## 电特性 ELECTRICAL CHARACTERISTICS

项 目 Parameter	符 号 Symbol	测试条件 Tests conditions	最小 Min	典型 Typ	最大 Max	单 位 Units
<b>关态特性 Off –Characteristics</b>						
漏—源击穿电压 Drain-Source Voltage	$BV_{DSS}$	$I_D=250\mu A, V_{GS}=0V$	600	-	-	V
击穿电压温度特性 Breakdown Voltage Temperature Coefficient	$\Delta BV_{DSS}/\Delta T_J$	$I_D=1mA$ , referenced to $25^\circ C$	-	0.60	-	V/ $^\circ C$
零栅压下漏极漏电流 Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=600V, V_{GS}=0V, T_C=25^\circ C$	-	-	10	$\mu A$
		$V_{DS}=480V, T_C=125^\circ C$	-	-	100	$\mu A$
正向栅极体漏电流 Gate-body leakage current, forward	$I_{GSSF}$	$V_{DS}=0V, V_{GS}=30V$	-	-	100	nA
反向栅极体漏电流 Gate-body leakage current, reverse	$I_{GSSR}$	$V_{DS}=0V, V_{GS}=-30V$	-	-	-100	nA
<b>通态特性 On-Characteristics</b>						
阈值电压 Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D=250\mu A$	2.0	-	4.0	V
静态导通电阻 Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=0.5A$	-	12	15	$\Omega$
正向跨导 Forward Transconductance	$g_{fs}$	$V_{DS}=40V, I_D=0.5$ (note 4)	-	0.6	-	S
<b>动态特性 Dynamic Characteristics</b>						
输入电容 Input capacitance	$C_{iss}$	$V_{DS}=25V, V_{GS}=0V, f=1.0MHz$	-	200	220	pF
输出电容 Output capacitance	$C_{oss}$		-	19	23	pF
反向传输电容 Reverse transfer capacitance	$C_{rss}$		-	2.8	4.0	pF





## 电特性 ELECTRICAL CHARACTERISTICS

开关特性 Switching Characteristics						
延迟时间 Turn-On delay time	$t_d(\text{on})$	$V_{DD}=300V, I_D=1.0A, R_G=25\Omega$ (note 4, 5)	-	9	20	ns
上升时间 Turn-On rise time	$t_r$		-	32	80	ns
延迟时间 Turn-Off delay time	$t_d(\text{off})$		-	16	41	ns
下降时间 Turn-Off Fall time	$t_f$		-	28	60	ns
栅极电荷总量 Total Gate Charge	$Q_g$	$V_{DS}=480V,$ $I_D=1.0A$ $V_{GS}=10V$ (note 4, 5)	-	2.5	3.5	nC
栅-源电荷 Gate-Source charge	$Q_{gs}$		-	0.5	-	nC
栅-漏电荷 Gate-Drain charge	$Q_{gd}$		-	1.2	-	nC
漏-源二极管特性及最大额定值 Drain-Source Diode Characteristics and Maximum Ratings						
正向最大连续电流 Maximum Continuous Drain -Source Diode Forward Current		$I_S$	-	-	1.0	A
正向最大脉冲电流 Maximum Pulsed Drain-Source Diode Forward Current		$I_{SM}$	-	-	4.0	A
正向压降 Drain-Source Diode Forward Voltage	$V_{SD}$	$V_{GS}=0V,$ $I_S=1.0A$	-	-	1.0	V
反向恢复时间 Reverse recovery time	$t_{rr}$	$V_{GS}=0V, I_S=1.0A$ $di_F/dt=100A/\mu s$ (note 4)	-	185	-	ns
反向恢复电荷 Reverse recovery charge	$Q_{rr}$		-	0.51	-	$\mu C$

## 热特性 THERMAL CHARACTERISTIC

项 目 Parameter	符 号 Symbol	最大 Max	单 位 Unit
		JCS1HN60TC	
结到管壳的热阻 Thermal Resistance, Junction to Case	$R_{th(j-c)}$	—	$^{\circ}C/W$
结到环境的热阻 Thermal Resistance, Junction to Ambient	$R_{th(j-A)}$	120	$^{\circ}C/W$

注释:

- 1: 脉冲宽度由最高结温限制
- 2:  $L=36mH, I_{AS}=1.0A, V_{DD}=50V, R_G=25\Omega$ , 起始结温  $T_J=25^{\circ}C$
- 3:  $I_{SD} \leq 1.0A, di/dt \leq 200A/\mu s, V_{DD} \leq BV_{DSS}$ , 起始结温  $T_J=25^{\circ}C$
- 4: 脉冲测试: 脉冲宽度  $\leq 300\mu s$ , 占空比  $\leq 2\%$
- 5: 基本与工作温度无关

Notes:

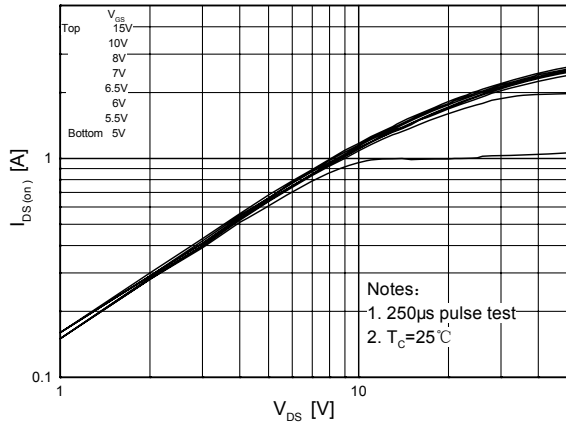
- 1: Pulse width limited by maximum junction temperature
- 2:  $L=36mH, I_{AS}=1.0A, V_{DD}=50V, R_G=25\Omega$ , Starting  $T_J=25^{\circ}C$
- 3:  $I_{SD} \leq 1.0A, di/dt \leq 200A/\mu s, V_{DD} \leq BV_{DSS}$ , Starting  $T_J=25^{\circ}C$
- 4: Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$
- 5: Essentially independent of operating temperature



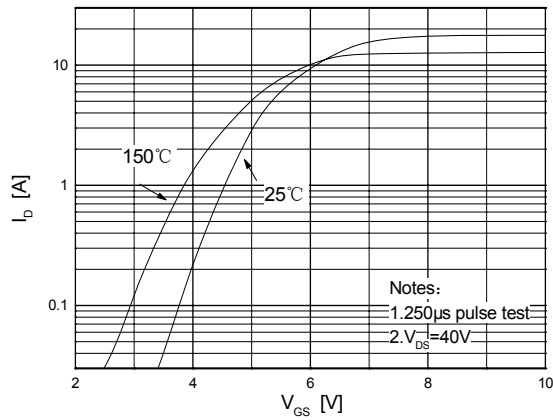


特征曲线 ELECTRICAL CHARACTERISTICS (curves)

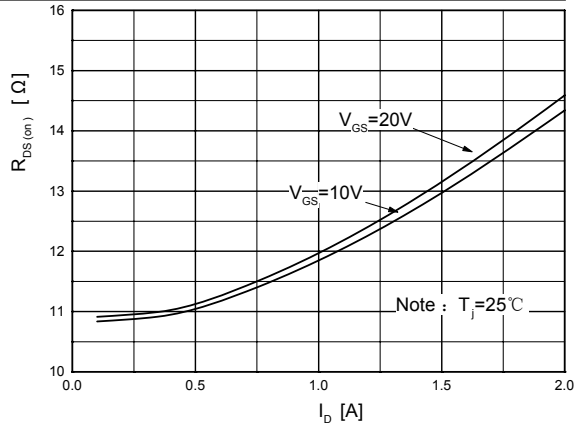
On-Region Characteristics



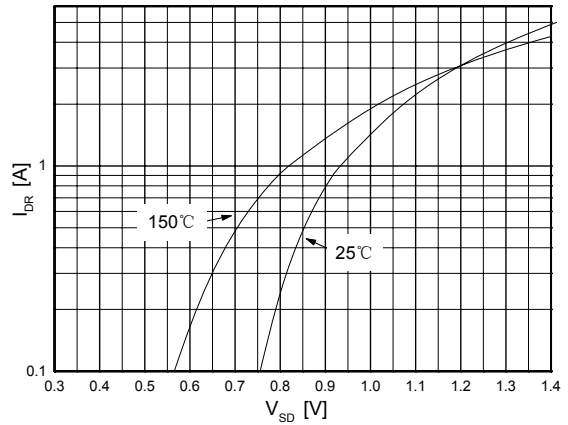
Transfer Characteristics



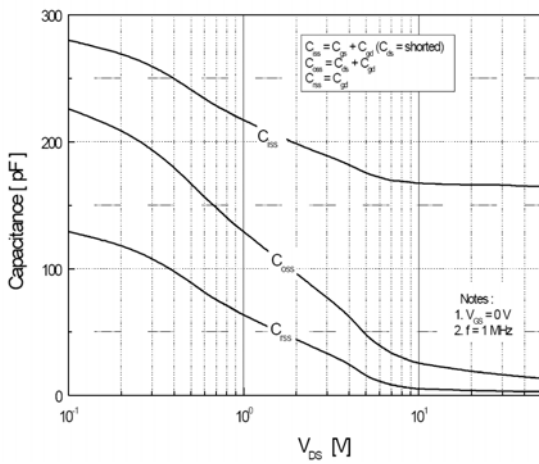
On-Resistance Variation vs. Drain Current and Gate Voltage



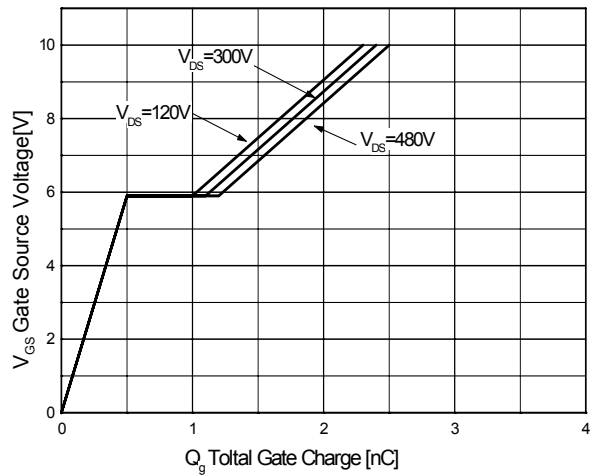
Body Diode Forward Voltage Variation vs. Source Current and Temperature



Capacitance Characteristics



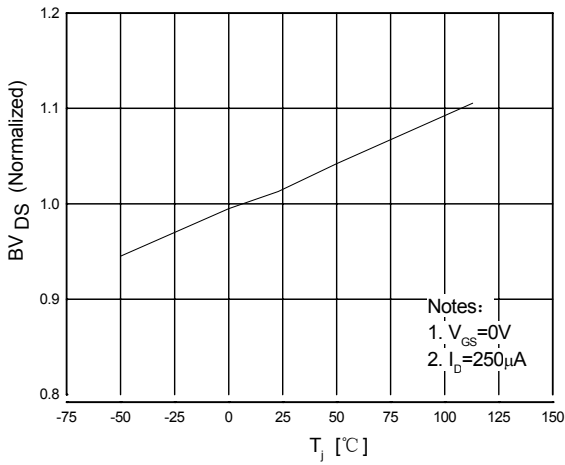
Gate Charge Characteristics



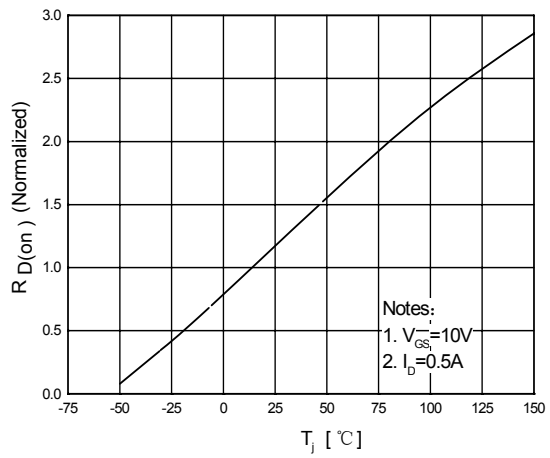


特征曲线 ELECTRICAL CHARACTERISTICS (curves)

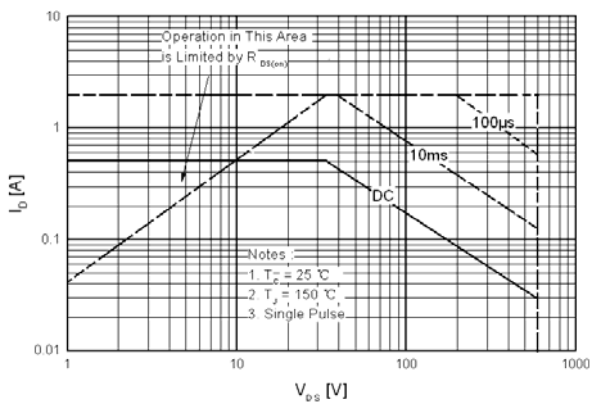
**Breakdown Voltage Variation vs. Temperature**



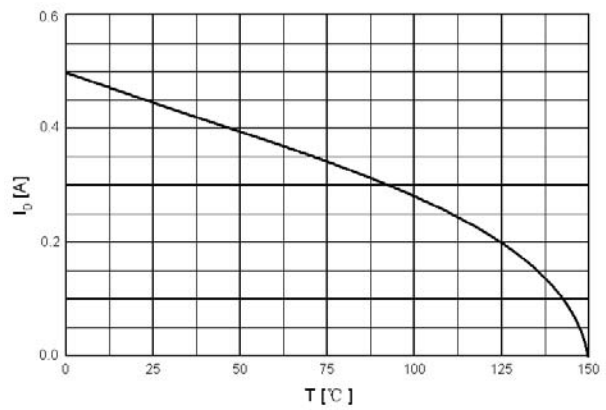
**On-Resistance Variation vs. Temperature**



**Maximum Safe Operating Area For JCS1HN60TC**

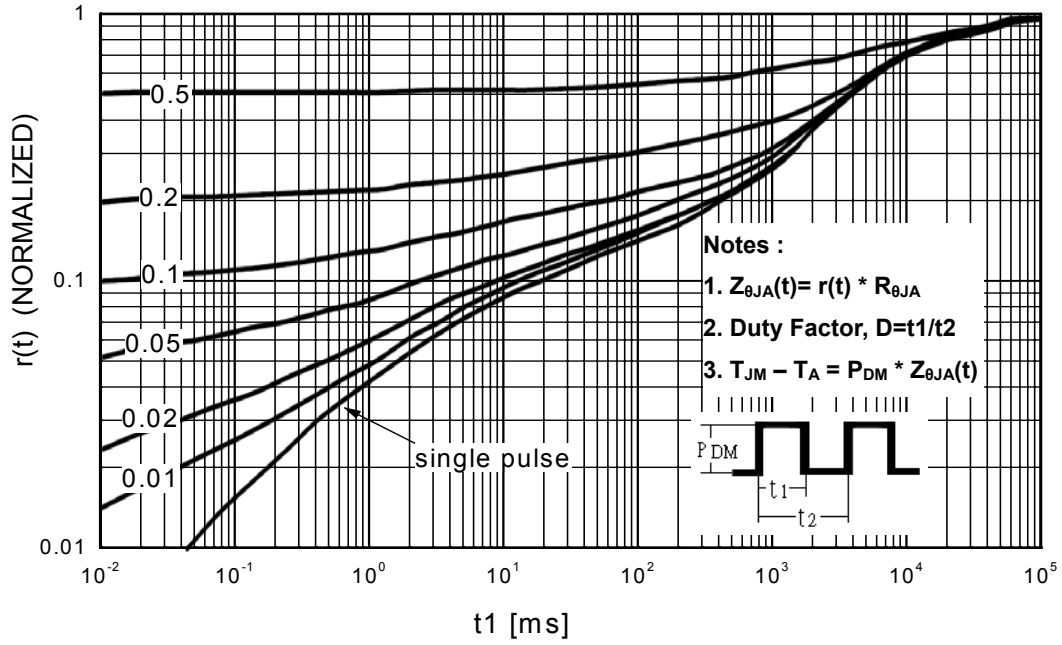


**Maximum Drain Current vs. Case Temperature**





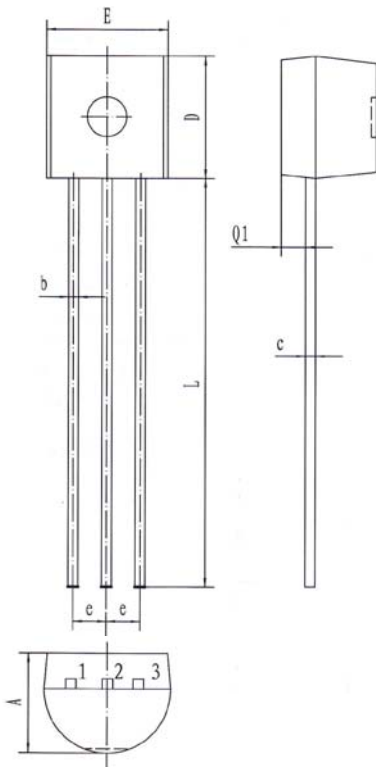
Transient Thermal Response Curve  
For JCS1HN60TC





TO-92

单位 Unit: mm



符号 symbol	MIN	MAX
A	3.30	3.90
b	0.35	0.55
c	0.31	0.51
D	4.30	4.90
E	4.30	4.90
e	1.17	1.37
L	12.50	15.50
Q1	0.74	0.89







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